

## **ABSTRACT OF THE DISCLOSURE**

A plurality of gate lines extending in a horizontal direction are formed on an insulating substrate, and a data line is formed perpendicular to the gate line thereby defining a pixel of a matrix array. Pixel electrodes receiving image signals through the data line are formed in a pixel, and a thin film transistor having a gate electrode connected to the gate line, a source electrode connected to the data line, and a drain electrode connected to the pixel electrode is formed on the portion where the gate lines and the data lines intersect. A storage wire including a storage electrode line is formed in the horizontal direction, and a storage electrode connected to the storage electrode line and forming a storage capacitance by overlapping the pixel electrode is formed in the pixel. A redundant repair line both ends of which overlap the storage wire of the neighboring pixel, and a storage wire connection line connecting the storage wires of a neighboring pixel are formed. In this structure, because the storage wires of a neighboring pixel are connected to each other through the storage wire connection line, the variation of the voltage for the storage capacitance may be minimized, and this results in a reduction of its distortion, such that crosstalk and flicker problems are minimized.